

Technical Data Sheet

5mm Silicon PIN Photodiode , T-1 3/4

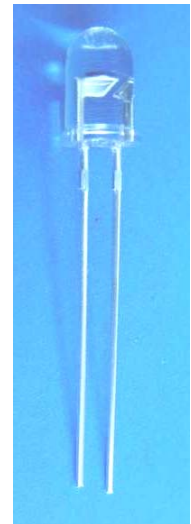
PD333-3C/H0/L2

Features

- Fast response time
- High photo sensitivity
- Small junction capacitance
- Pb free
- The product itself will remain within RoHS compliant version.

Descriptions

PD333-3C/H0/L2 is a high speed and high sensitive PIN photodiode in a standard 5 ϕ plastic package. Due to its water clear epoxy the device is sensitive to visible and infrared radiation.

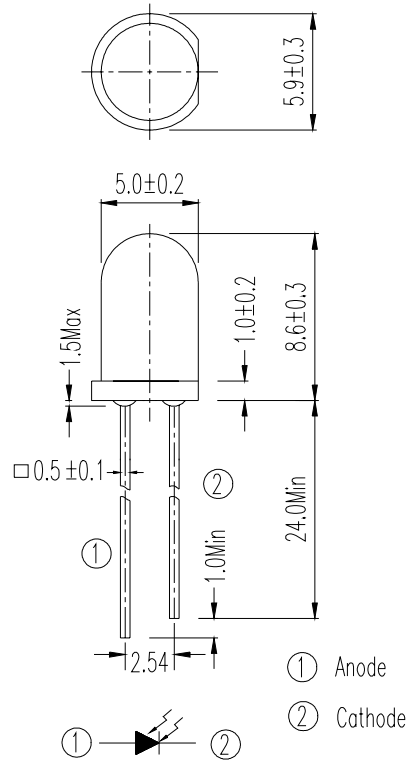


Applications

- High speed photo detector
- Security system
- Camera

Device Selection Guide

LED Part No.	Chip	Lens Color
	Material	
PD	Silicon	Water clear

Package Dimensions

- Notes:** 1.All dimensions are in millimeters
2.Tolerances unless dimensions ± 0.25 mm

Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Rating	Units
Reverse Voltage	V_R	32	V
Power Dissipation	P_d	150	mW
Lead Soldering Temperature	T_{sol}	260	°C
Operating Temperature	T_{opr}	-25 ~ +85	°C
Storage Temperature	T_{stg}	-40 ~ +85	°C

- Notes:** *1:Soldering time ≤ 5 seconds.
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Electro-Optical Characteristics (Ta=25°C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Units
Rang of Spectral Bandwidth	$\lambda_{0.5}$	-----	400	---	1100	nm
Wavelength of Peak Sensitivity	λ_p	-----	---	940	---	nm
Open-Circuit Voltage	V_{OC}	Ee=5m W/cm ² $\lambda_p=940\text{nm}$	---	0.39	---	V
Short- Circuit Current	I_{SC}	Ee=1m W/cm ² $\lambda_p=940\text{nm}$	---	40	---	μA
Reverse Light Current	I_L	Ee=1m W/cm ² $\lambda_p=940\text{nm}$ $V_R=5\text{V}$	36	40	---	
Dark Current	I_d	Ee=0m W/cm ² $V_R=10\text{V}$	---	5	30	nA
Reverse Breakdown	BV_R	Ee=0m W/cm ² $I_R=100\mu\text{A}$	32	170	---	V
Total Capacitance	C_t	Ee=0m W/cm ² $V_R=5\text{V}$ $f=1\text{MHZ}$	---	18	---	pF
Rise/Fall Time	t_r/t_f	$V_R=10\text{V}$ $R_L=1\text{K}\Omega$	---	45/45	---	nS
View Angle	$2\theta_{1/2}$	$I_F=20\text{mA}$	--	80	--	deg

Typical Electro-Optical Characteristics Curves

Fig.1 Power Dissipation vs. Ambient Temperature

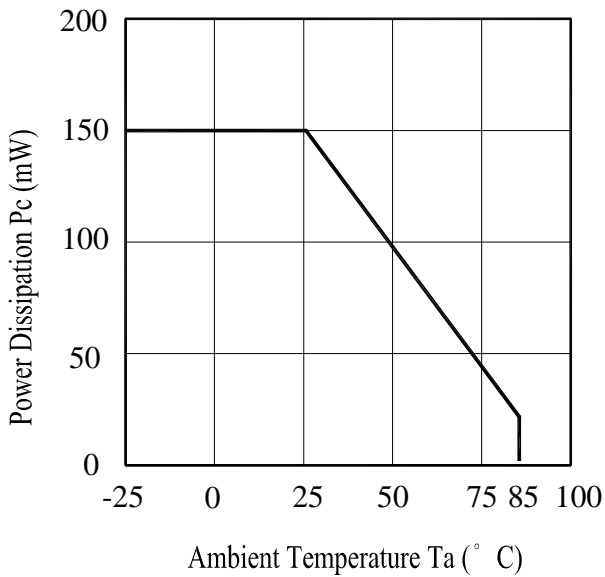


Fig.2 Spectral Sensitivity

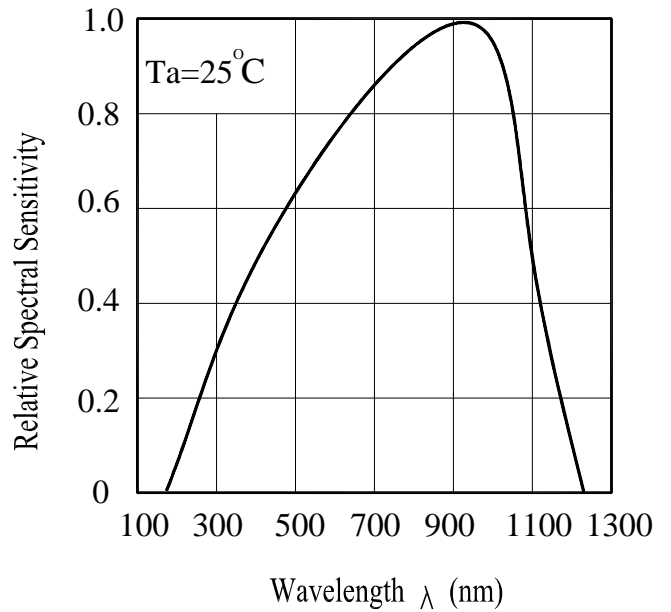


Fig.3 Dark Current vs. Ambient Temperature

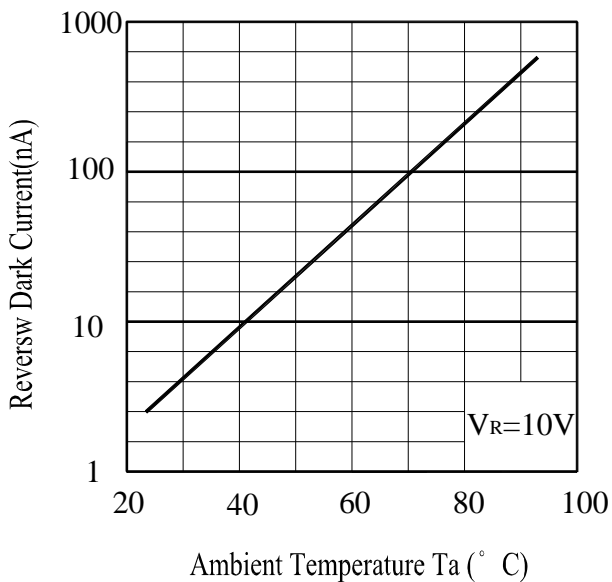
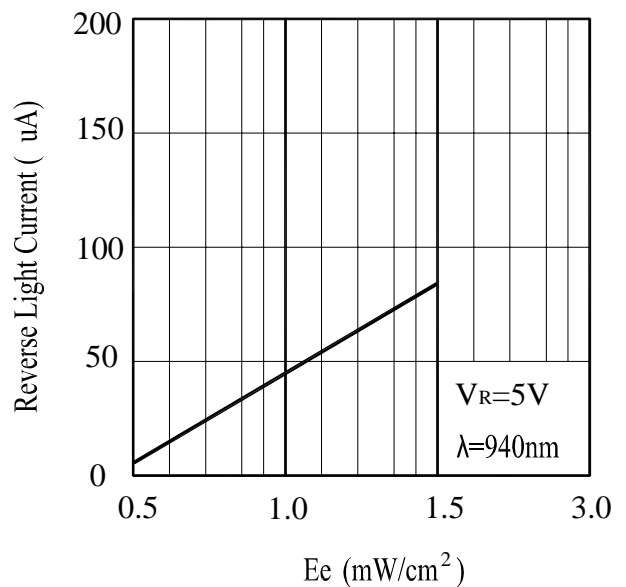


Fig. 4 Reverse Light Current vs. Ee



Typical Electro-Optical Characteristics Curves

Fig.5 Terminal Capacitance vs.

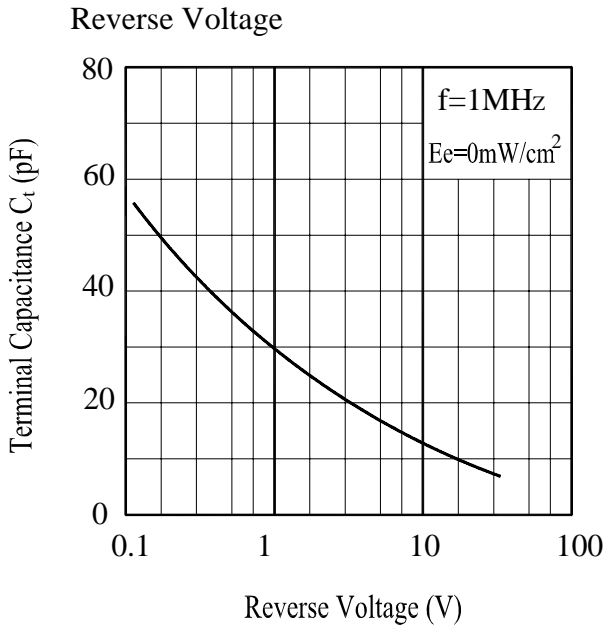


Fig.6 Response Time vs.

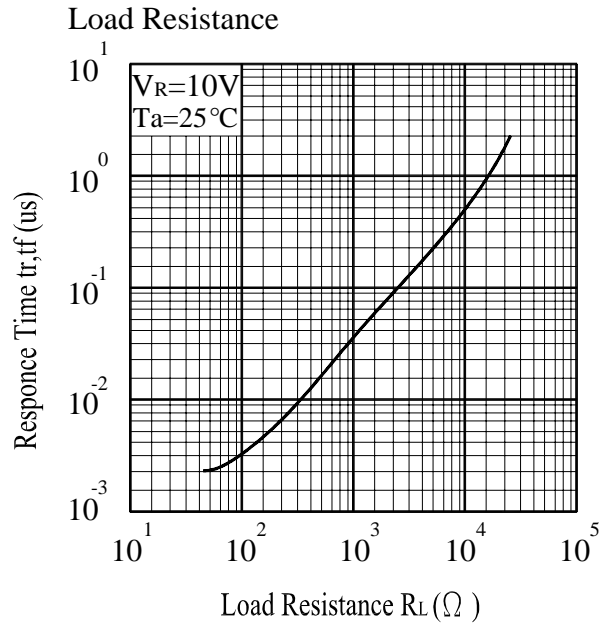


Fig.7 Relative Reverse Light Current vs. Ambient Temperature($^\circ\text{C}$)

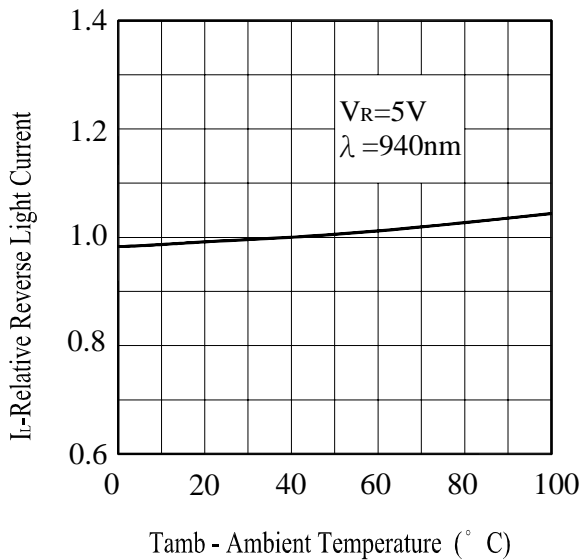
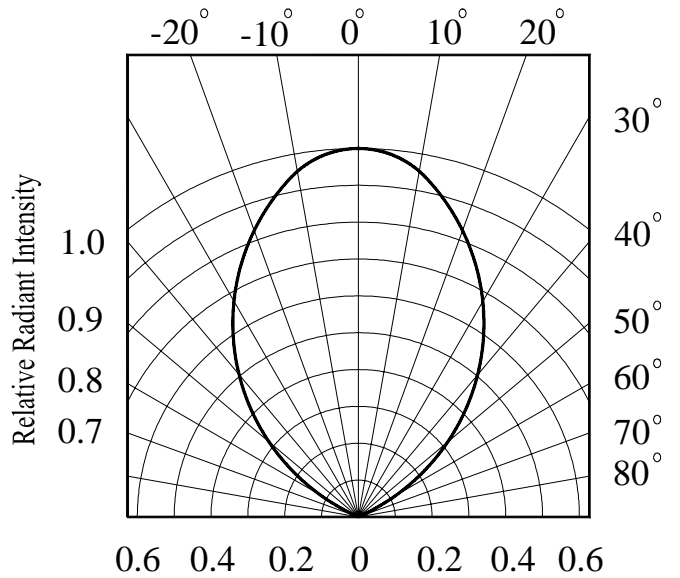


Fig.8 Relative Radiant Intensity vs. Angular Displacement



Packing Quantity Specification

1.500PCS/1Bag , 5Bags/1Box

2.10Boxes/1Carton

Label Form Specification



CPN: Customer's Production Number

P/N : Production Number

QTY: Packing Quantity

CAT: Ranks

HUE: Peak Wavelength

REF: Reference

LOT No: Lot Number

MADE IN TAIWAN: Production Place